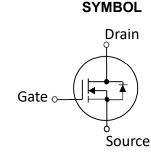


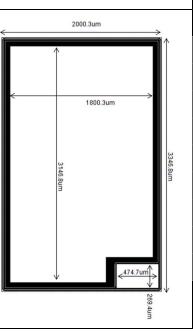
40V, 195A ⁽¹⁾ N-Channel MOSFET

- Proprietary Trench Gate Device Design and Processes
- High Reliability Capability
- Sampled CP Probing and Inking



Electrica	Electrical Characteristics in C/P Test (TJ at 25 ℃)					
Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Condition
V _{(BR)DSS}	Drain-Source Breakdown Voltage	40			V	V _{GS} =0V, I _D =250µA
R _{DS(ON)}	Static Drain-Source On-Resistance	_	1.1	1.3	mΩ	$V_{GS} = 10V, I_{D} = 1A(2)$
V _{GS (th)}	Gate Threshold Voltage	1		2.5	V	V_{DS} = V_{GS} , I_D =250 μ A
I _{DSS}	Drain-to-Source Leakage Current	_	_	1	μA	V _{DS} =32V, V _{GS} =0V
I _{GSS}	Gate-to-Source Leakage Current	-100	_	100	nA	V _{DS} =0V, V _{GS} =±20V
T _J , T _{STG}	Operating and Storage Temperature		-55℃ to 150℃ Max.			

Mechanical Data Die Drawing Chip Size 2000 µm X 3347 µm Gate Pad Size 475 µm X 270 µm Source Pad Size 1800 µm X 3147 µm Scribe Line Width 60 µm Wafer Thickness 150 µm Wafer Diameter 200 mm 4021 EA Gross Die Source Metallization Al-Cu (4µm typical) **Drain Metallization** Ti-Ni-Ag Passivation SiN Store in original container, in dry nitrogen, 6 **Recommended Storage** months at ambient temperature of 23°C ± 3°C Environment



(1) This characteristic assumes the die is assembled in DFN5*6 package. Actual performance may degrade when assembled.

(2) Pulse Width tp = < 1 mS, Duty Cycle < 2%.



Specific Assembly Info	ormation Bill of Material (BOM)	Die Drawing
Package Type	DFN5*6	2000.3um
Die Attach Method	Soft solder	<
Soft Solder Composition	Pb,Sn,Ag	1800.3um
Gate Wire Bonding	Cu, 2 mil x1	3345.8um 3146.8um
Source Wire Bonding	60mil*4mil Al Ribbon (double stitch)	5
Molding Compound Manufacturer	G700HF	√ < <u>474.7um</u> }
Solder Plating Composition	Pure Tin	269.4um

Position		Bonding Diagram Top View		
	X (um)	Y (um)	ZERO	
ZERO	0	0		
ТОР	3346.8	2000.3		
S1	100	100		
S2	2970	1900.3		
S3	3246.8	1420		
G1	3045.13	1495.75	52 53 61 62 63	
G2	3314.53	1970.45	ţ	

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Condition
IDSS	Drain-to-Source Leakage Current	_	_	1	μA	V _{DS} =32V, V _{GS} =0V
Igssf	Gate-to-Source Leakage Current	_		100	nA	V _{DS} =0V, V _{GS} =+20V
Igssr	Gate-to-Source Leakage Current	-100			nA	V _{DS} =0V, V _{GS} =-20V
BV _{DSS}	Drain-Source Breakdown Voltage	40			V	V _{GS} =0V, I _D =250µA
BV _{DSS}	Drain-Source Breakdown Voltage	40	_	_	V	V_{GS} =0V, I_D =1mA
RDS(ON)	Static Drain-Source On-Resistance	_	_	2.6	mΩ	V _{GS} =10V, I _D =20A
V _{GS (th)}	Gate Threshold Voltage	1		2.5	V	V_{DS} = V_{GS} , I_D =250 μ A
V_{SD}	Drain-Source Diode Forward Voltage			1.1	V	V_{GS} = 0V, I_{SD} = 20A
EAS test	IAS				А	VDD=40V,Vgs=10V, RG=25ohm,L=0.5mH
Tj, Tstg	Operating and Storage Temperature	-55℃ to 150℃ Max.				



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